1. Record Nr. UNISA996451649103316

Autore	FOLDES, Stephan <1951->
Titolo	Fundamental structures of algebra and discrete mathematics / Stephan Foldes
Pubbl/distr/stampa	New York, : Wiley, 1994
ISBN	9781118033180
Descrizione fisica	Testo elettronico (PDF) (XV, 344 p.)
Disciplina	512.02
Soggetti	Algebra
Lingua di pubblicazione	Inglese
Formato	Risorsa elettronica
Livello bibliografico	Monografia
Sommario/riassunto	Introduce e chiarisce le teorie di base di 12 concetti strutturali, offrendo una teoria fondamentale di gruppi, anelli e altre strutture algebriche. Identifica gli elementi essenziali e descrive le interrelazioni tra teorie particolari. Teoremi classici selezionati e risultati rilevanti per la ricerca attuale sono dimostrati rigorosamente all'interno della teoria di ciascuna struttura. In tutto il testo il lettore è spesso invitato a svolgere esercizi integrati di verifica e ad esplorare esempi.

2. Record Nr. UNIORUON00382987

Autore	CARINI, Isidoro
Titolo	Sulle scienze occulte nel Medioevo / Isidoro Carini - rist. anast
Pubbl/distr/stampa	Sala Bolognese, : Arnaldo Forni, stampa 1983 - XXXII, 97 p., ; 22 cm. - Rist anast. dell'ed. : Palermo, : stamperia Perino, 1872
Disciplina	133
Soggetti	SCIENZE OCCULTE - Medioevo
Lingua di pubblicazione	Italiano
Formato	Materiale a stampa
Livello bibliografico	Monografia

3. Record Nr. UNINA9910955859403321

Autore	Lee-Schoenfeld Vera
Titolo	Beyond coherence : the syntax of opacity in german
Pubbl/distr/stampa	Amsterdam, : John Benjamins, 2007
ISBN	9786612152627 9781282152625 1282152629 9789027291974 9027291977
Edizione	[1st ed.]
Descrizione fisica	1 online resource (vii, 206 pages) : illustrations
Collana	Linguistik aktuell = Linguistics today ; ; v. 114
Disciplina	435
Soggetti	German language - Syntax German language - Infinitival constructions German language - Possessives
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Bibliographic Level Mode of Issuance: Monograph
Nota di contenuto	Beyond Coherence; Editorial page; Title page; LCC data; Table of Contents; Preface; Introduction; I. Reduced Infinitive Constructions; II. The Possessor Dative Construction; III. Coherence By Phase; Appendix

	A; Appendix B; Bibliography; Name Index; Subject Index; The series Linguistik Aktuell/Linguistics Today
Sommario/riassunto	The overarching theme of this volume is one of the central concerns of syntactic theory: How local is syntax, and what are the measures of syntactic locality? It is argued here that movement and anaphoric relations are governed by a unified concept of locality: the phase.

4.

Record Nr.	UNINA9910826220503321
Autore	Deen M. Jamal
Titolo	Silicon photonics : fundamentals and devices / / M.J. Deen, P.K. Basu
Pubbl/distr/stampa	Chichester, West Sussex, UK ; ; Hoboken, N.J., : Wiley, 2012
ISBN	9786613695079 9781119940906 1119940907 9781280784682 1280784687 9781119945154 1119945151 9781119945161 111994516X
Edizione	[1st edition]
Descrizione fisica	1 online resource (455 p.)
Collana	Wiley Series in Materials for Electronic & Optoelectronic Applications
Altri autori (Persone)	BasuP. K (Prasanta Kumar)
Disciplina	621.38152
Soggetti	Silicon - Optical properties Optoelectronic devices Photonics
Lingua di pubblicazione	Inglese
Formato	Materiale a stampa
Livello bibliografico	Monografia
Note generali	Description based upon print version of record.
Nota di bibliografia	Includes bibliographical references and index.
Nota di contenuto	Silicon Photonics: Fundamentals and Devices; Contents; Series Preface; Preface; 1 Introduction to Silicon Photonics; 1.1 Introduction; 1.2 VLSI: Past, Present, and Future Roadmap; 1.3 The Interconnect Problem in VLSI; 1.4 The Long-Haul Optical Communication Link; 1.4.1 Basic Link and Components; 1.4.2 Materials and Integration; 1.5 Data Network;

1.6 Conclusions; 1.7 Scope of the Book; References; 2 Basic Properties of Silicon; 2.1 Introduction; 2.2 Band Structure; 2.2.1 E-k Diagram: General Considerations; 2.2.2 Band Properties near Extremas; 2.2.3 Refined Theory for Band Structures
2.2.4 Temperature- and Pressure-Dependent Band Gap 2.2.5 Band Structure in Ge; 2.3 Density-of-States Function; 2.4 Impurities; 2.4.1 Donors and Acceptors; 2.4.2 Isoelectronic Impurities; 2.5 Alloys of Silicon and Other Group IV Elements; 2.5.1 Different Alloy Systems; 2.5.2 Lattice Constants; 2.5.3 Band Structures of Unstrained Alloys; 2.6 Heterojunctions and Band Lineup; 2.7 Si-Based Heterostructures; 2.7.1 Lattice-Mismatched Heteroepitaxy; 2.7.2 Pseudomorphic Growth and Critical Thickness; 2.7.3 Elasticity Theory: Stress and Strain; 2.7.4 Expressions for Critical Thickness
2.7.5 Strain Symmetric Structures and Virtual Substrates 2.7.6 Band Offsets and Band Lineup; 2.7.7 Electronic Properties of SiGe/Si Heterostructures; 2.8 Direct Gap: Ge/SiGeSn Heterojunctions; 2.8.1 Structures; 2.8.2 Band Edges and Band Lineup; Problems; References; Suggested Readings; 3 Quantum Structures; 3.1 Introduction; 3.2 Quantum Wells; 3.2.1 Condition for Quantum Confinement; 3.2.2 A Representative Structure; 3.2.3 Simplified Energy Levels; 3.2.4 Density-of-States in Two Dimensions; 3.2.5 Finite Quantum Well; 3.2.6 Refined Methods; 3.2.7 Different Band Alignments
3.3 Quantum Wires and Dots 3.3.1 Subbands and DOS in Quantum Wires; 3.3.2 Quantum Dots; 3.4 Superlattices; 3.5 Si-Based Quantum Structures; 3.5.1 Electron Subband Structure; 3.5.2 Hole Subbands; 3.5.3 Quantum Wells and Barriers; 3.6 Effect of Electric Field; Problems; References; Suggested Readings; 4 Optical Processes; 4.1 Introduction; 4.2 Optical Constants; 4.3 Basic Concepts; 4.3.1 Absorption and Emission; 4.3.2 Absorption and Emission Rates; 4.4 Absorption Processes in Semiconductors; 4.5 Fundamental Absorption in Direct Gap; 4.5.1 Conservation Laws
4.5.2 Calculation of Absorption Coefficient 4.6 Fundamental Absorption in Indirect Gap; 4.6.1 Theory of Absorption; 4.6.2 Absorption Spectra in Si; 4.6.3 Absorption Spectra in Ge; 4.7 Absorption and Gain; 4.8 Intervalence Band Absorption; 4.9 Free-carrier Absorption; 4.10 Recombination and Luminescence; 4.10.1 Luminescence Lifetime; 4.10.2 Carrier Lifetime: Dependence on Carrier Density; 4.10.3 Absorption and Recombination; 4.10.4 Microscopic Theory of Recombination; 4.11 Nonradiative Recombination; 4.11.1 Recombination via Traps; 4.11.2 Auger Recombination; 4.11.3 Surface Recombination
4.11.4 Recombination of Complexes

Sommario/riassunto

The creation of affordable high speed optical communications using standard semiconductor manufacturing technology is a principal aim of silicon photonics research. This would involve replacing copper connections with optical fibres or waveguides, and electrons with photons. With applications such as telecommunications and information processing, light detection, spectroscopy, holography and robotics, silicon photonics has the potential to revolutionise electronic-only systems. Providing an overview of the physics, technology and device operation of photonic devices using exclusively silicon